

Ronald Green

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

17
papers

463
citations

10
h-index

18
g-index

18
ext. papers

536
ext. citations

0.8
avg, IF

3.49
L-index

#	Paper	IF	Citations
17	Influence of High-Temperature Bias Stress on Room-Temperature VT Drift Measurements in SiC Power MOSFETs. <i>Materials Science Forum</i> , 2019 , 963, 757-762	0.4	2
16	Measurement considerations for evaluating BTI effects in SiC MOSFETs. <i>Microelectronics Reliability</i> , 2018 , 81, 121-126	1.2	21
15	SiC MOSFET threshold-stability issues. <i>Materials Science in Semiconductor Processing</i> , 2018 , 78, 32-37	4.3	26
14	Influences of Bias Interruption and Reapplication on High-Temperature Threshold-Voltage Shifts of SiC DMOSEFETs. <i>Materials Science Forum</i> , 2018 , 924, 743-747	0.4	2
13	Feasibility of SiC Threshold Voltage Drift Characterization for Reliability Assessment in Production Environments. <i>Materials Science Forum</i> , 2017 , 897, 509-512	0.4	8
12	Comparison of Test Methods for Proper Characterization of VT in SiC MOSFETs. <i>Materials Science Forum</i> , 2016 , 858, 833-839	0.4	14
11	Bias-Temperature-Stress Response of Commercially-Available SiC Power MOSFETs. <i>Materials Science Forum</i> , 2015 , 821-823, 677-680	0.4	4
10	Radiation-Induced Trapped Charging Effects in SiC Power MOSFETs. <i>Materials Science Forum</i> , 2014 , 778-780, 533-536	0.4	2
9	A Study of High Temperature DC and AC Gate Stressing on the Performance and Reliability of Power SiC MOSFETs. <i>Materials Science Forum</i> , 2013 , 740-742, 549-552	0.4	11
8	Evaluation of PBTS and NBTS in SiC MOS Using In Situ Charge Pumping Measurements. <i>Materials Science Forum</i> , 2013 , 740-742, 545-548	0.4	12
7	Detection of Mobile Ions in the Presence of Charge Trapping in SiC MOS Devices. <i>Materials Science Forum</i> , 2012 , 717-720, 461-464	0.4	10
6	Two-Way Tunneling Model of Oxide Trap Charging and Discharging in SiC MOSFETs. <i>Materials Science Forum</i> , 2012 , 717-720, 465-468	0.4	32
5	Application of reliability test standards to SiC Power MOSFETs 2011 ,		46
4	High-Temperature Reliability of SiC Power MOSFETs. <i>Materials Science Forum</i> , 2011 , 679-680, 599-602	0.4	36
3	(Invited) Implications for Robust Reliability Testing of Power SiC MOSFETs. <i>ECS Transactions</i> , 2011 , 41, 215-224	1	
2	Time Dependence of Bias-Stress-Induced SiC MOSFET Threshold-Voltage Instability Measurements. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 1835-1840	2.9	205
1	Temperature-Dependence of SiC MOSFET Threshold-Voltage Instability. <i>Materials Science Forum</i> , 2008 , 600-603, 807-810	0.4	32

